

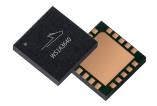
# GaN on SiC Power Amplifier Module for 5G

## **Description**

The WS1A3940 is an Asymmetric Doherty Power Amplifier Module (PAM) integrating Wolfspeed GaN on SiC HEMT transistors with RF matching and biasing networks on a multilayer laminate substrate with advanced heat sinking technology. The WS1A3940 has been designed to operate from 3700 MHz to 3980 MHz, from supply voltages up to 50 V, at average output power levels of 8 to 10 W with crest-factor reduced and digitally pre-distorted LTE and 5G NR signals with instantaneous bandwidths of 200 MHz or more. The device is housed in a 6 mm X 6 mm land grid array (LGA) package.

#### **Features**

- GaN on SiC technology
- Frequency: 3700-3980 MHz
- Average Output Power: 39.5 dBm
- P<sub>SAT</sub> = 48 dBm
- RF inputs matched to  $50 \Omega$  and DC matched
- Gate bias supply for main and peak sides available from either side of device
- · Integrated harmonic terminations
- Pb-free and RoHS compliant



WS1A3940 Package PG-LGA-6x6-3-1

## **Typical Broadband Performance**

 $\label{eq:single-carrier} \textbf{Single-carrier LTE Performance} \ (\text{tested in Wolfspeed applications circuit for } 3700-4100\ \text{MHz}) \\ V_{DD} = 48\ \text{V, } I_{DQ(main)} = 45\ \text{mA, } V_{GS(peak)} = -5.1\ \text{V, channel bandwidth} = 20\ \text{MHz, input PAR} = 10\ \text{dB} \ @\ 0.01\%\ \text{CCDF} = 10\ \text{MHz} = 10\ \text{dB} \ @\ 0.01\%\ \text{CCDF} = 10\ \text{dB} =$ 

	P <sub>OUT</sub> (dBM)	Gain (dB)	Efficiency (%)	ACPR – (dBc)	ACPR + (dBc)	PAR (dB)
3700 MHz	39.5	14.5	53.0	-26	-26	8.3
3850 MHz	39.5	13.7	52.0	-30	-30	8.5
3980 MHz	39.5	12.9	51.0	-32	-32	8.5
4100 MHz	39.5	11.7	48.5	-29	-29	8.0



# Maximum Ratings at T<sub>CASE</sub> = 25 °C

Parameter		Symbol	Value	Unit
Drain-source Voltage		$V_{DSS}$	125	V
Gate-source Voltage		$V_{GS}$	-10 to +2	V
Operating Voltage		$V_{DD}$	55	V
RF Input Power (main)	Pulse CW, 10% duty cycle,	P <sub>IN</sub>	35.2	dBm
(peak)	20 μs pulse width	$P_{IN}$	38	dBm
Case Temperature		T <sub>C</sub>	135	°C
Storage Temperature Range		T <sub>STG</sub>	-65 to +150	°C

Operation above the maximum values listed here may cause permanent damage. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the component. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. For reliable continuous operation, the device should be operated within the operating voltage range (V<sub>DD</sub>) specified above.

#### **DC Characteristics**

Characteristics	Conditions	Symbol	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage (main)	$V_{GS} = -8 \text{ V}, I_D = 3.36 \text{ mA}$	V <sub>(BR)DSS</sub>	150	_	_	V
(peak)	$V_{GS} = -8 \text{ V}, I_D = 5.6 \text{ mA}$	$V_{(BR)DSS}$	150	_	_	V
Gate Leakage Current	$V_{GS} = -8 \text{ V}, V_{DS} = 50 \text{ V}$	I <sub>GSS</sub>	_	_	-1.5	mA
Gate Threshold Voltage (main)	$V_{DS} = 10 \text{ V}, I_D = 3.36 \text{ mA}$	V <sub>GS(th)</sub>	-3.8	-3.0	-2.3	V
(peak)	$V_{DS} = 10 \text{ V}, I_D = 5.6 \text{ mA}$	$V_{GS(th)}$	-3.6	-2.7	-2	V

# **Recommended Operating Conditions**

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Operating Voltage		$V_{DD}$	0	_	50	V
Gate Quiescent Voltage (main)	$V_{DS} = 48 \text{ V}, I_{D} = 30 \text{ mA}$	$V_{GS(Q)}$	-3.6	-3.1	-2.6	V
(peak)	$V_{DS} = 48 \text{ V}, I_D = 40 \text{ mA}$	$V_{GS(Q)}$	-3.6	-3.1	-2.6	V

## **Moisture Sensitivity Level**

Level	el Test Standard		Unit
3	IPC/JEDEC J-STD-020	260	°C

## **ESD Characteristics**

Parameter	Class	Standard
Human Body Model (HBM)	Class 1B	ANSI/ESDA/JEDEC JS-001
Charge Device Model (CDM)	Class C3	ANSI/ESDA/JEDEC JS-002

## **RF Characteristics** (tested in Wolfspeed production test fixture)

 $V_{DD}$  = 48 V, Pulse CW 10% duty cycle, 20  $\mu$ s pulse width

Danamatan	Cl	Canaditions	Ma	ain	Pe	ak	Unit
Parameter	Symbol	Conditions	Min	Max	Min	Max	Unit
3700 MHz							
Gain	G	P <sub>OUT</sub> = 38 dBm (main) P <sub>OUT</sub> = 37.5 dBm (peak)	13	16.3	12.5	16.5	dB
Saturated Power	P <sub>SAT</sub>	$P_{SAT}$ $I_{DQ} = 30 \text{ mA (main)}$ $I_{DQ} = 40 \text{ mA (peak)}$		-	43	_	dBm
Efficiency Eff		$I_{DQ}$ = 30 mA (main), $P_{SAT}$ $I_{DQ}$ = 40 mA (peak), $P_{SAT}$	45	-	34	-	%
3980 MHz							
Gain	G	P <sub>OUT</sub> = 38 dBm (main) P <sub>OUT</sub> = 37.5 dBm (peak)	12	16	10	14	dB
Saturated Power	P <sub>SAT</sub>	$P_{SAT}$ $I_{DQ} = 30 \text{ mA (main)}$ $I_{DQ} = 40 \text{ mA (peak)}$		_	41	-	dBm
Efficiency Eff $I_{DQ} = 30 \text{ mA (main)}, P_{SAT}$ $I_{DQ} = 40 \text{ mA (peak)}, P_{SAT}$		46	-	31	-	%	

# **Ordering Information**

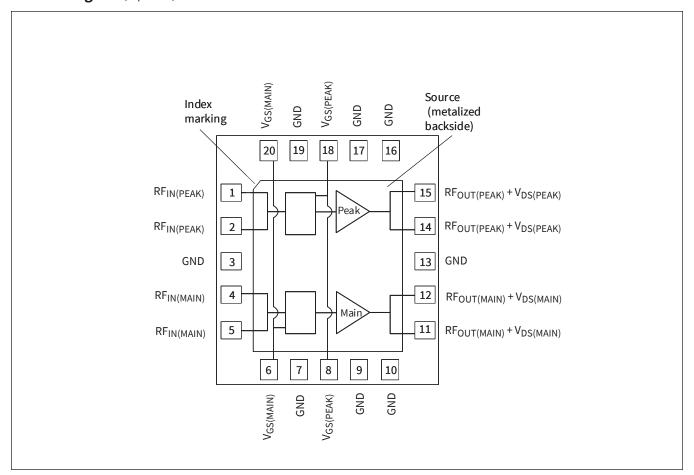
Order Code	Description
WS1A3940-V2-R00A	Sample Quantities
WS1A3940-V2-R1	330 mm (13") Reel 100 pcs
WS1A3940-V2-R3K	330 mm (13") Reel 3,000 pcs
FXA/ WSGPA01V1-18	3.7-3.98 GHz Driver Evaluation Board
FXA/WS1A3940V2-04	3.7-3.98 GHz Evaluation Board

# **Evaluation Boards - Typical RF Performance**

Part Number Frequency		P <sub>OUT</sub> (dBm)	Eff (%)	Gain (dB)	PAR (dB)	ACPR+ (dBc)	ACPR- (dBc)	
Output Stage: WS1A3940 Single-carrier WCDMA Performance, V <sub>DD</sub> = 48 V, I <sub>DQ(main)</sub> = 45 mA, channel bandwidth = 3.84 MHz, input PAR = 10 dB @ 0.01% CCDF								
FXA/WS1A3940V2-04	3.7-3.98 GHz	39.5	44.5	29.8	8	-27.5	-27.5	

<b>WSGPA01 Driver</b> Single-carrier WCDMA Pe	rformance, V <sub>DD</sub> = 48 V, I <sub>DQ</sub> = 25 m/	A, channel bandwidth	= 3.84 MHz, i	nput PAR = 10	dB @ 0.01%	CCDF	
FXA/WSGPA01V1-18	3.7-3.98 GHz	26.5	17.5	16.8	9.1	-46.3	-45.2

## Pinout Diagram (top view)



## **Bias Sequencing**

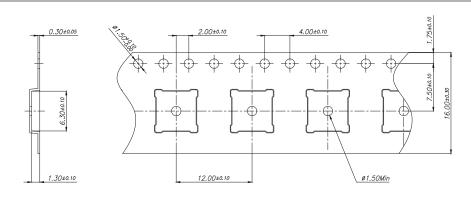
#### **Bias ON**

- 1. Ensure RF is turned off
- 2. Apply pinch-off voltage of –5 V to the gate
- 3. Apply nominal drain voltage
- 4. Bias gate to desired quiescent drain current
- 5. Apply RF

#### **Bias OFF**

- 1. Turn RF off
- 2. Apply pinch-off voltage to the gate
- 3. Turn-off drain voltage
- 4. Turn-off gate voltage

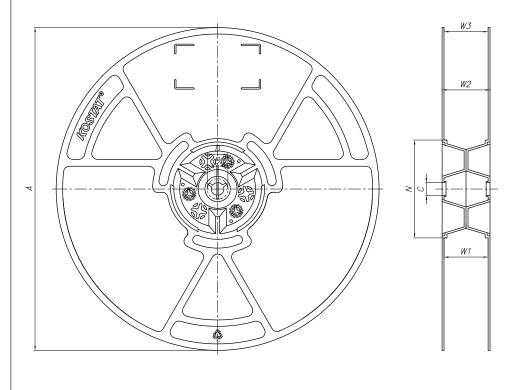
## **Tape and Reel Information**

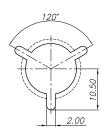




- (I) 10 sprocket hole pitch cumulative tolerance ± 0.20
- (II) Camber not to exceed 1 mm in 250 mm
- (III) Material: Black conductive Polystyrene
- (IV) Ao and Bo measured on a plane 0.3 mm above the bottom of the pocket.
- (V) Ko measured from a plane on the inside bottom of the pocket to the top surface of the carrier
- (VI) Pocket position relative to sprocket hole measured as true position of pocket, not pocket hole

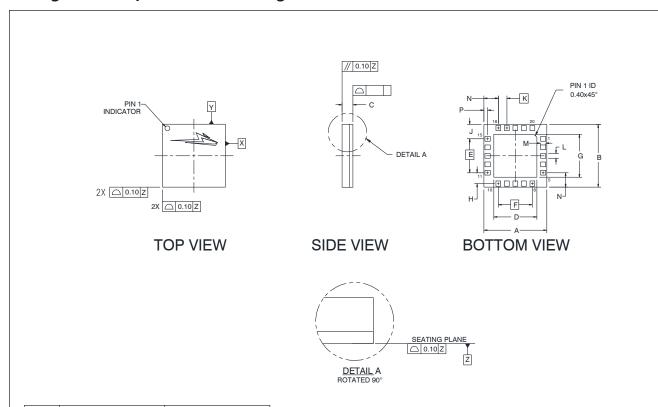
ALL DIMENSIONS IN MILLIMETERS UNLESS OTHERWISE STATED.





Size	А	В	С	D	N	W1	W2	W3
16mm	330 <sup>+2.0</sup> <sub>-2.0</sub>	1.5min	13.0 <sup>+0.5</sup> <sub>-0.2</sub>	20.2 min	100 <sup>+3.0</sup> <sub>-0.0</sub>	16.4 <sup>+2.0</sup> <sub>-0.0</sub>	20.4 +2.0 -2.0	17.65 <sup>+1.75</sup> <sub>-1.75</sub>

## Package Outline Specifications - Package PG-LGA-6x6-3-1



	INCHES			MI	ILLIMETER	RS
DIM	MIN	TYP	MAX	MIN	TYP	MAX
Α	.234	.236	.238	5.95	6.00	6.05
В	.234	.236	.238	5.95	6.00	6.05
С	.037	.041	.045	0.93	1.03	1.13
D	.157	.161	.165	4.00	4.10	4.20
Е	_	.128	_	_	3.24	_
F	_	.128	_	_	3.24	_
G	_	.161	_	-	4.10	_
Н	_	.041	_	-	1.03	_
J	.054	.054	.055	1.37	1.38	1.39
K	_	.032	_	-	0.81	_
L	_	.018	_	_	0.46	_
М	_	.020	_		0.50	_
N	.054	.054	.055	1.37	1.38	1.39
Р	.013	.014	.014	0.34	0.35	0.36

Diagram Notes-unless otherwise specified:

1. Interpret dimensions and tolerances per ASME Y14.5M-1994.